

L Number	Hits	Search Text	DB	Time stamp
1	29	(semiconductor near3 laser) and (reverse\$3 with bias\$3) same (tunnel with junction)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 18:33
2	27	((semiconductor near3 laser) and (reverse\$3 with bias\$3) same (tunnel with junction)) and active	USPAT; EPO; JPO; IBM_TDB	2003/11/23 18:33
8	13	(semiconductor near4 laser) and (c with axis with revers\$4)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:41
9	269	wurtzite and laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:41
10	15	wurtzite with axis and semiconductor near3 laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
11	0	wurtzite same axis same revers\$3 same c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
12	0	wurtzite same axis same revers\$3	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
13	60	wurtzite same axis same c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:44
14	43	wurtzite with axis with c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:44
15	2	(wurtzite with axis with c) and c with revers\$4	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:52
16	14	(wurtzite with axis with c) and semiconductor near3 laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:45
17	1	(revers\$4 with c with axis) same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
18	0	revers\$4 same "c-axis" same nitrogen same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
19	0	revers\$4 same "c-axis" same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:56
20	106	revers\$4 same "c-axis"	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
21	19	(revers\$4 same "c-axis") and ("N" nitrogen) with (face side surface)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:55
22	65259	GaN same c-axis sme (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:56
23	5	GaN same c-axis same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:03
24	120	((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:04
26	10	((((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction) and polarization	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:04
27	2	("5418374" "6414976").PN.	USPAT	2003/11/23 20:06

25	68	(((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:21
28	1	5814531.URPN.	USPAT	2003/11/23 20:08
29	8	("4404678" "4569721" "4946802" "5149670" "5202285" "5255281" "5336635" "5375136").PN.	USPAT	2003/11/23 20:08
30	8	("4404678" "4569721" "4946802" "5149670" "5202285" "5255281" "5336635" "5375136").PN.	USPAT	2003/11/23 20:13
31	52	(((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) not (((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:23
32	172	372/43-50.ccls. and (tilt\$3 angl\$4) near5 active	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:25
33	143	(372/43-50.ccls. and (tilt\$3 angl\$4) near5 active) not (((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser))	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:24
34	9	372/43-50.ccls. and (tilt\$3 near5 active)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:25
35	1	5693965.URPN.	USPAT	2003/11/23 20:27
36	3	("3888388" "4520485" "5602864").PN.	USPAT	2003/11/23 20:27